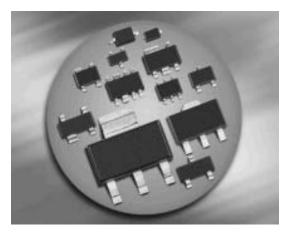


Silicon Variable Capacitance Diodes

- Frequency range up to 2 GHz
- Special design for use in TV-sat tuners
- Pb-free (RoHS compliant) package¹⁾
- Qualified according AEC Q101





BB831

Туре	Package	Configuration	L _S (nH)	Marking
BB831	SOD323	single	1.8	white T

Maximum Ratings at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit V	
Diode reverse voltage	V _R	30		
Peak reverse voltage	V _{RM}	35		
$(R \ge 5 k\Omega)$				
Forward current	/ _F	20	mA	
Operating temperature range	T _{op}	-55 125	°C	
Storage temperature	T _{stg}	-55 150		

¹Pb-containing package may be available upon special request



Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics	•	•			
Reverse current	I _R				nA
<i>V</i> _R = 30 V		-	-	20	
$V_{\rm R} = 30 \text{ V}, \ T_{\rm A} = 85 \text{ °C}$		-	-	500	
AC Characteristics					
Diode capacitance	CT				pF
$V_{\rm R} = 1 {\rm V}, f = 1 {\rm MHz}$		7.8	8.8	9.8	
$V_{\rm R}$ = 28 V, f = 1 MHz		0.85	1.02	1.2	
Capacitance ratio	C _{T1} /C _{T28}	7.8	8.6	9.5	
$V_{\rm R} = 1 \text{ V}, V_{\rm R} = 28 \text{ V}, f = 1 \text{ MHz}$					
Capacitance matching ¹⁾	$\Delta C_{\rm T}/C_{\rm T}$	-	-	3	%
$V_{\rm R}$ = 1 V, $V_{\rm R}$ = 28 V, f = 1 MHz					
Series resistance	r _S	-	1	-	Ω
<i>V</i> _R = 1 V, <i>f</i> = 100 MHz					

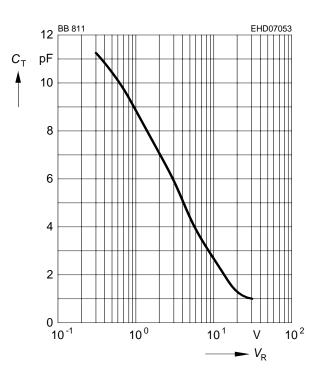
Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

¹For details please refer to Application Note 047.



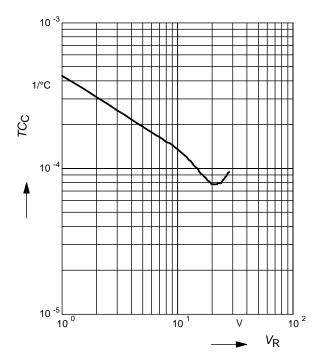
Diode capacitance $C_{T} = f(V_{R})$

f = 1 MHz

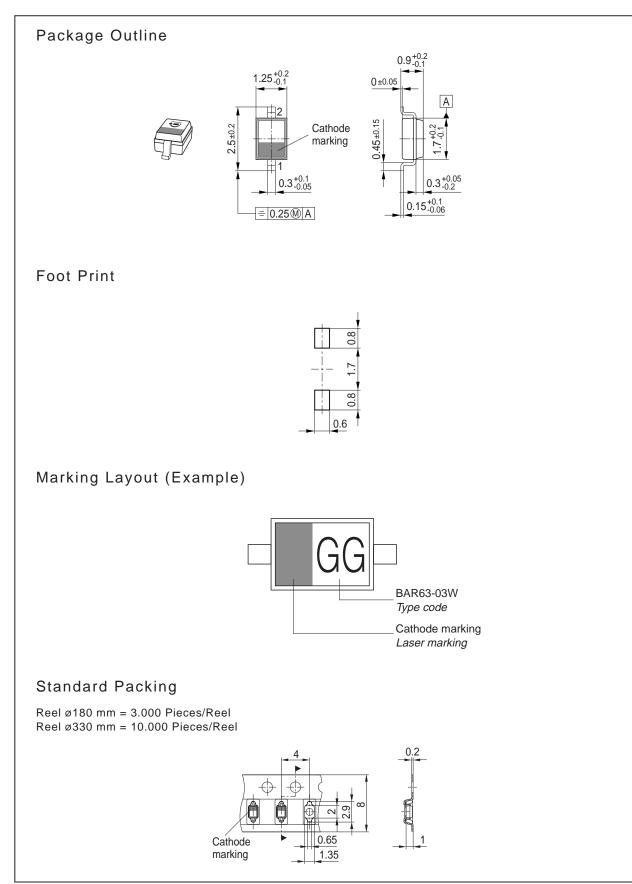


Temperature coefficient of the diode

capacitance $T_{Cc} = f(V_R)$









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